DA121TT1G

Silicon Switching Diode

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Continuous Reverse Voltage	V_R	80	V
Recurrent Peak Forward Current	I_F	200	mA
Peak Forward Surge Current Pulse Width = 10 μs	$I_{FM(surge)}$	500	mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, FR-4 Board (Note 1) T_A = 25°C Derated above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	555	°C/W
Total Device Dissipation, FR-4 Board (Note 2) T_A = 25°C Derated above 25°C	P_D	360 2.9	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	345	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-4 @ Minimum Pad
2. FR-4 @ 1.0 × 1.0 Inch Pad

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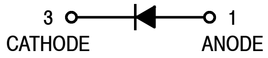
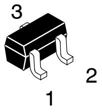
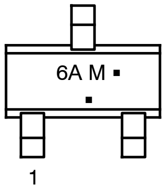




SOT-416 / SC-75
CASE 463
STYLE 2

MARKING DIAGRAM



6A = Specific Device Code
M = Date Code*
▪ = Pb-Free Package
(Note: Microdot may be in either location)

*Date Code orientation and/or orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
DA121TT1G	SOT-416 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Forward Voltage – (I_F = 1.0 mA) (I_F = 10 mA) (I_F = 50 mA) (I_F = 150 mA)	V_F	 – – – –	 715 866 1000 1250	mV
Reverse Current – (V_R = 75 V) (V_R = 75 V, T_J = 150°C) (V_R = 25 V, T_J = 150°C)	I_R	 – – –	 1.0 50 30	μA
Capacitance – (V_R = 0, f = 1.0 MHz)	C_D	–	2.0	pF
Reverse Recovery Time – (I_F = I_R = 10 mA, R_L = 50 Ω) (Figure 1)	t_{rr}	–	6.0	ns
Stored Charge – (I_F = 10 mA to V_R = 6.0 V, R_L = 500 Ω) (Figure 2)	QS	–	45	PC
Forward Recovery Voltage – (I_F = 10 mA, t_r = 20 ns) (Figure 3)	V_{FR}	–	1.75	V

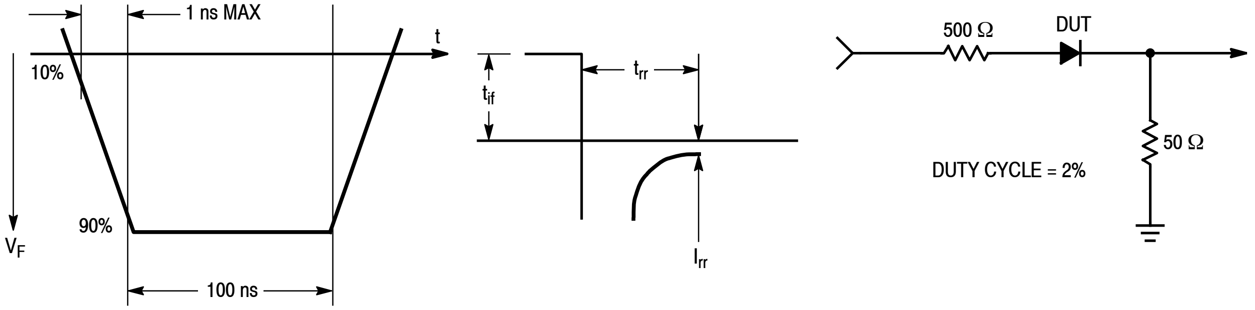


Figure 1. Reverse Recovery Time Equivalent Test Circuit

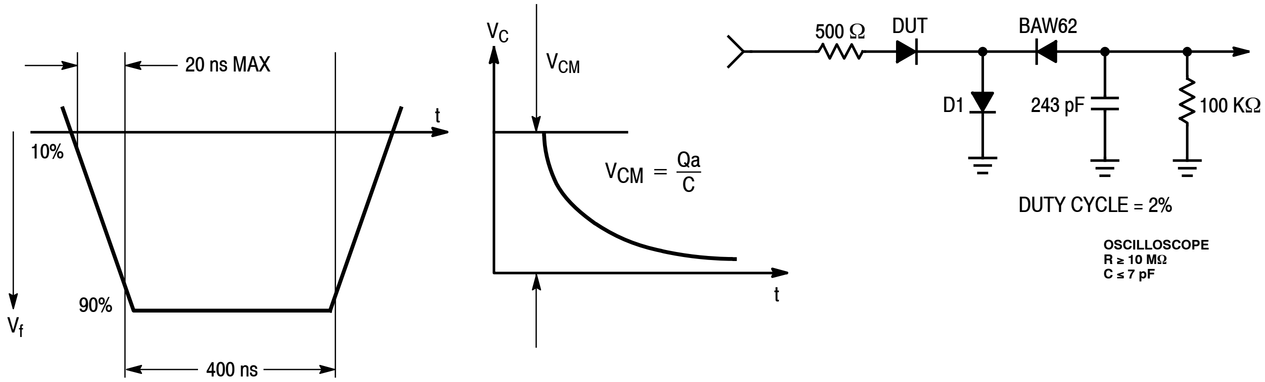


Figure 2. Recovery Charge Equivalent Test Circuit

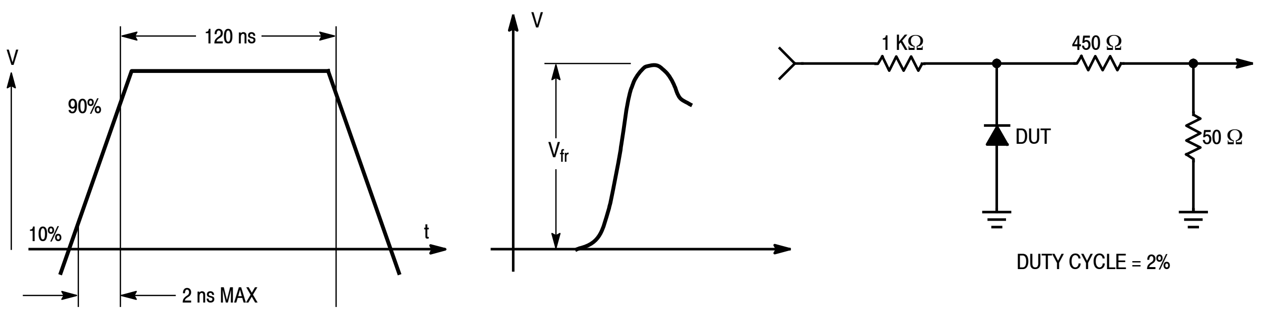


Figure 3. Forward Recovery Voltage Equivalent Test Circuit

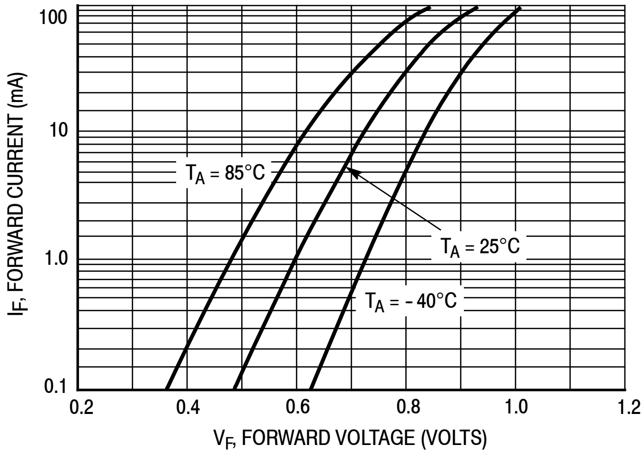


Figure 4. Forward Voltage

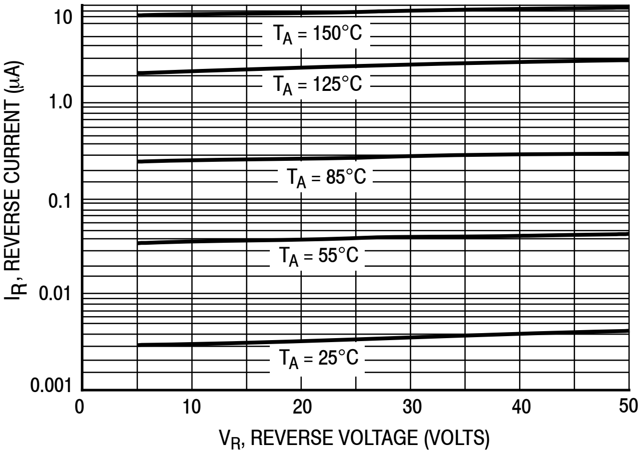


Figure 5. Leakage Current

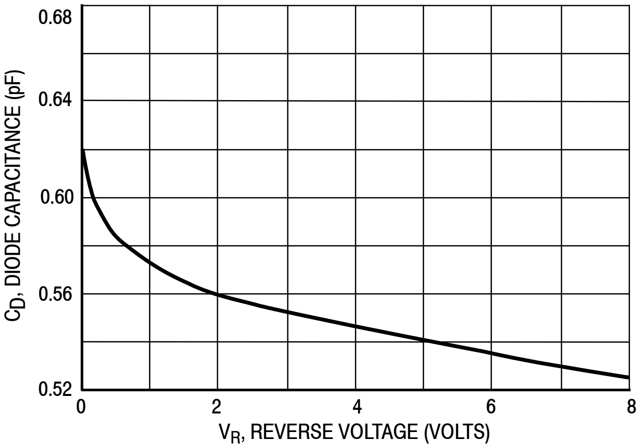


Figure 6. Capacitance

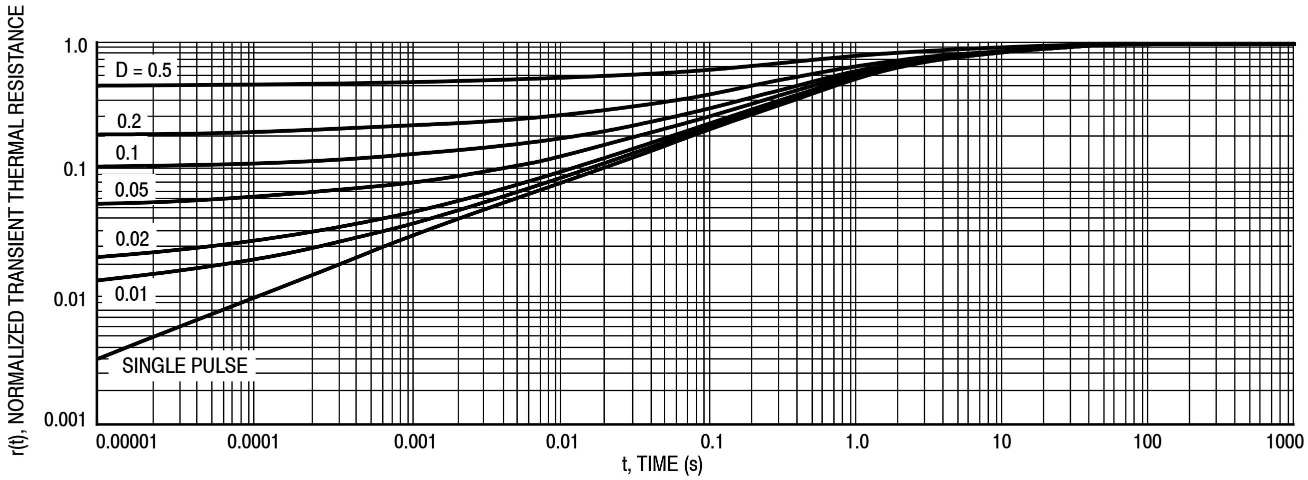


Figure 7. Normalized Thermal Response

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

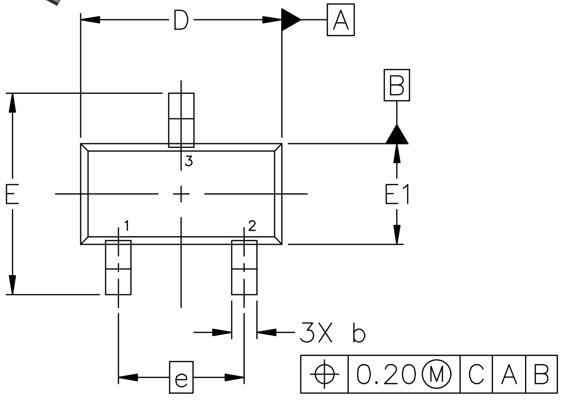
SC75−3 1.60x0.80x0.80, 1.00P
CASE 463
ISSUE H

DATE 01 FEB 2024

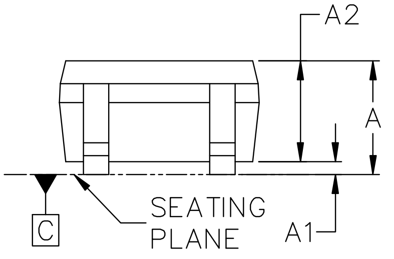
NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5−2018.
2. ALL DIMENSION ARE IN MILLIMETERS.

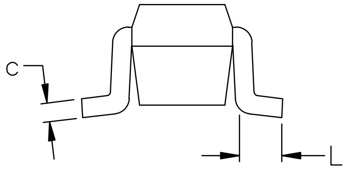
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.80	0.90
A1	0.00	0.05	0.10
A2	0.80 REF.		
b	0.15	0.20	0.30
c	0.10	0.15	0.25
D	1.55	1.60	1.65
E	1.50	1.60	1.70
E1	0.70	0.80	0.90
e	1.00 BSC		
L	0.10	0.15	0.20



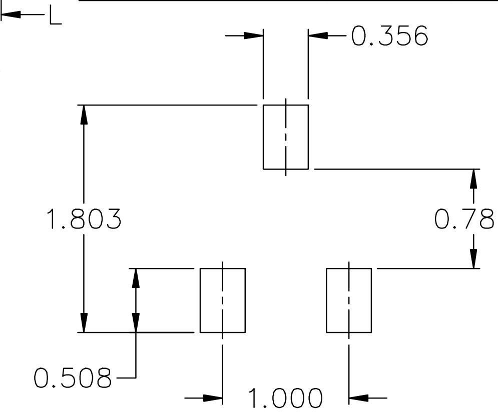
TOP VIEW



SIDE VIEW



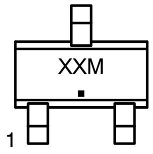
END VIEW



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

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DESCRIPTION:	**SC75−3 1.60x0.80x0.80, 1.00P**	**PAGE 1 OF 1**

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